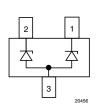


Two-Line ESD Protection in SOT-23





FEATURES

- Two-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge
- Space saving SOT-23 package
- AEC-Q101 qualified
- e3 Sn
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

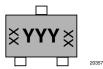




COMPLIANT HALOGEN **FREE**



MARKING (example only)



YYY = type code (see table below) XX = date code

ORDERIN	ORDERING INFORMATION											
	EN	/IRONMENTAL AN	ENTAL AND QUALITY CODE		PACKAG	ING CODE						
PART NUMBER (EXAMPLE)	AEC-Q101			TIN	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)					
(250 22)	QUALIFIED	STANDARD	GREEN							10K/BOX = MOQ		
GSOT05C-		Е		3	-08		GSOT05C-E3-08					
GSOT05C-			G	3	-08		GSOT05C-G3-08					
GSOT05C-	Н	Е		3	-08		GSOT05C-HE3-08					
GSOT05C-	Н		G	3	-08		GSOT05C-HG3-08					
GSOT05C-		Е		3		-18	GSOT05C-E3-18					
GSOT05C-			G	3		-18	GSOT05C-G3-18					
GSOT05C-	Н	E		3		-18	GSOT05C-HE3-18					
GSOT05C-	Н		G	3		-18	GSOT05C-HG3-18					



PACKA	GE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
GSOT03C	SOT-23	03C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G30103C	301-23	C1G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terrilliais
GSOT04C	SOT-23	04C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G301040	301-23	C8G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terrilliais
GSOT05C	SOT-23	05C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G30103C	301-23	C2G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terrilliais
GSOT08C	SOT-23	08C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G30108C	301-23	C3G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terrilliais
GSOT12C	SOT-23	12C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G301120	301-23	C4G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terrimais
GSOT15C	SOT-23	15C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
GSOTISC	301-23	C5G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terminals
GSOT24C	SOT-23	24C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G301240	301-23	C6G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	200 O/ TO S at terminals
GSOT36C	SOT-23	36C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301300	301-23	C7G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	200 O/ TO S at terminals

ABSOLUTE MAXIMUM RATINGS GSOT03C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I	30	Α		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	30	Α		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P_PP	369	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	грр	504	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT04C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I	30	Α		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	30	А		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	429	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	564	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT05C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	· I _{PPM}	30	А		
r eak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	тРРМ	30	А		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	480	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, t _p = 8/20 µs; single shot	Lbb	612	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
ESD IIIIIIdility	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT08C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I	18	А		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	Іррм	18	А		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P_PP	345	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	400	W		
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT12C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	· I _{PPM}	12	А		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	тРРМ	12	Α		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	312	W		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	грр	337	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD .	± 30	kV		
Operating temperature	Junction temperature	T _J	- 55 to + 150	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT15C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	lan	8	А	
r ear puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, t_p = 8/20 μ s; single shot	ІРРМ	8	А	
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	345	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	400	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV	
ESD IIIIIIuriity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C	
Storage temperature		T _{STG}	- 55 to + 150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT24C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Deal and a compart	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	lane.	5	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	5	А		
Deal of land of	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	235	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	240	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM	RATINGS GSOT36C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	J	3.5	А
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I _{PPM}	3.5	А
Poak pulso powor	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	248	W
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	252	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
ESD initiduity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C
Storage temperature		T _{STG}	- 55 to + 150	°C



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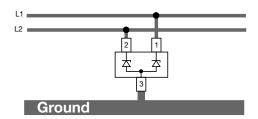
BIAs-MODE (2-line Bidirectional Asymmetrical protection mode)

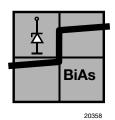
With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage (V_{RWM}) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).

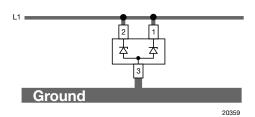




If a higher surge current or peak pulse current (I_{PP}) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to "double" the performance.

This offers:

- double surge power = double peak pulse current (2 x I_{PPM})
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance (2 x C_D)
- double reverse leakage current (2 x I_R)



ELECTRICAL CHARACTERISTICS GSOT03C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines	
Reverse stand-off voltage	at I _R = 100 μA	V_{RWM}	-	-	3.3	V	
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μA	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4	4.6	-	V	
Reverse clamping voltage	at I _{PP} = 1 A	\/	-	5.7	7.5	V	
heverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V	
Forward elemping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V	
Capacitance	at V _R = 0 V; f = 1 MHz		-	420	600	pF	
Сараспансе	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF	



ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines	
Reverse stand-off voltage	at I _R = 20 μA	V_{RWM}	-	-	4	V	
Reverse current	at V _R = 4 V	I _R	-	-	20	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5	6.1	-	V	
Reverse clamping voltage	at I _{PP} = 1 A	V	-	7.5	9	V	
heverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	11.2	14.3	V	
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	VF	-	4.5	-	V	
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	- C _D	-	310	450	pF	
Оараспансе	at V _R = 2 V; f = 1 MHz	OD	-	200	-	pF	

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 10 μA	V_{RWM}	-	-	5	V		
Reverse current	at V _R = 5 V	I _R	-	-	10	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6	6.8	-	V		
Payaraa alamning valtaga	at I _{PP} = 1 A	V _C	-	7	8.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	VC	-	12	16	V		
Forward elemping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	VF	-	4.5	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	- C _D	-	260	350	pF		
Capacitance	at V _R = 2.5 V; f = 1 MHz		-	150	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 5 μA	V_{RWM}	-	-	8	V		
Reverse current	at V _R = 8 V	I _R	-	-	5	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9	10	-	V		
Poverse elemping veltage	at I _{PP} = 1 A	.,	-	10.7	13	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _C	-	15.2	19.2	V		
Forward elemping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _F	-	3	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	0	-	160	250	pF		
Capacitance	at V _R = 4 V; f = 1 MHz	- C _D	-	80	-	pF		



ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	12	V		
Reverse current	at V _R = 12 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15	-	V		
Reverse clamping voltage	at I _{PP} = 1 A	.,	-	15.4	18.7	V		
neverse ciamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	21.2	26	V		
Forward elemping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 12 A	VF	-	2.2	-	V		
	at V _R = 0 V; f = 1 MHz		-	115	150	pF		
Capacitance	at V _R = 6 V; f = 1 MHz	- C _D	-	50	-	pF		

ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	15	V		
Reverse current	at V _R = 15 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.5	18	-	V		
Deverse elemening veltage	at I _{PP} = 1 A	.,	-	19.4	23.5	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _C	-	24.8	28.8	V		
Forward elemping voltage	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _F	-	1.8	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz		-	90	120	pF		
Capacitance	at V _R = 7.5 V; f = 1 MHz	- C _D	-	35	-	pF		

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	24	V		
Reverse current	at V _R = 24 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27	30	-	V		
Dovorgo alampina valtago	at I _{PP} = 1 A	.,	-	34	41	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V		
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 5 A	VF	-	1.4	-	V		
Capacitance	at V _R = 0 V; f = 1 MHz	0	-	65	80	pF		
Оараспансе	at V _R = 12 V; f = 1 MHz	- C _D	1	20	-	pF		

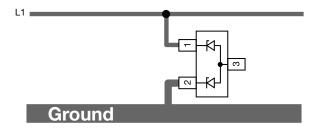


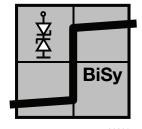
ELECTRICAL CHARACTERISTICS GSOT36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	36	V		
Reverse current	at V _R = 36 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39	43	-	V		
Reverse clamping voltage	at I _{PP} = 1 A		-	49	60	V		
heverse clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _C	-	59	71	V		
Conveyed elemening veltage	at I _{PP} = 1 A		-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _F	-	1.3	-	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	52	65	pF		
Сараспансе	at V _R = 18 V; f = 1 MHz		-	12	-	pF		

BISy-MODE (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).





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ELECTRICAL CHARACTERISTICS GSOT03C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 100 μA	V_{RWM}	-	-	3.8	V		
Reverse current	at V _R = 3.8 V	I _R	-	-	100	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4.5	5.3	-	V		
Poverse elemping voltage	at I _{PP} = 1 A	V _C	-	7	8.4	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	v _C	-	14	16.8	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	210	300	pF		
	at V _R = 1.6 V; f = 1 MHz		-	190	-	pF		



ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 20 μA	V_{RWM}	-	-	4.5	V		
Reverse current	at V _R = 4.5 V	I _R	-	-	20	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5.5	6.8	-	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	7.5	9	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	v _C	-	15.7	18.8	V		
0	at V _R = 0 V; f = 1 MHz	- C _D	-	155	225	pF		
Capacitance	at V _R = 2 V; f = 1 MHz		-	135	-	pF		

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 10 μA	V_{RWM}	-	-	5.5	V		
Reverse current	at V _R = 5.5 V	I _R	-	-	10	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6.5	7.5	-	V		
Poverse elemping veltage	at I _{PP} = 1 A	Vc	-	8.1	9.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	VC	-	17	20.4	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	130	175	pF		
	at $V_R = 4 V$; $f = 1 MHz$		-	100	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 5 μA	V_{RWM}	-	-	8.5	V		
Reverse current	at V _R = 8.5 V	I _R	-	-	5	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9.5	10.7	-	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	11.7	14	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	v _C	-	18.5	22.2	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	80	125	pF		
	at V _R = 4 V; f = 1 MHz		-	60	-	pF		

ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	ı	-	12.5	V		
Reverse current	at V _R = 12.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15.7	-	٧		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	16.4	19.7	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	v _C	-	23.4	28.1	V		
Conscitores	at $V_R = 0 V$; $f = 1 MHz$	- C _D	-	58	75	pF		
Capacitance	at V _R = 7.5 V; f = 1 MHz		-	36	-	pF		



ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	15.5	V		
Reverse current	at V _R = 15.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	17	18.7	-	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	20.4	24.5	V		
neverse clamping voltage	at $I_{PP} = I_{PPM} = 8 A$	v _C	-	26.6	30.6	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	45	60	pF		
	at V _R = 7.5 V; f = 1 MHz		-	25	-	pF		

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	24.5	V			
Reverse current	at V _R = 24.5 V	I _R	-	-	1	μΑ			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27.5	30.7	-	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	34	41	V			
	at I _{PP} = I _{PPM} = 5 A		-	40	48	V			
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	33	40	pF			
	at V _R = 12 V; f = 1 MHz		-	18	-	pF			

ELECTRICAL CHARACTERISTICS GSOT36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	at I _R = 1 μA	V_{RWM}	-	-	36.5	V			
Reverse current	at V _R = 36.5 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39.5	43.7	-	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	50	60	V			
	at I _{PP} = I _{PPM} = 3.5 A		-	60	72	V			
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	26	33	pF			
	at V _R = 18 V; f = 1 MHz		-	10	-	pF			



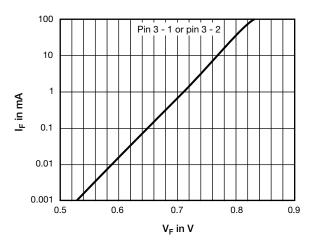


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

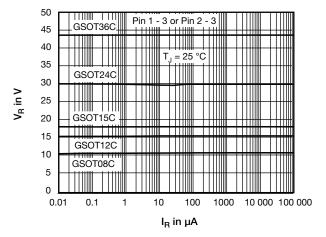


Fig. 2 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

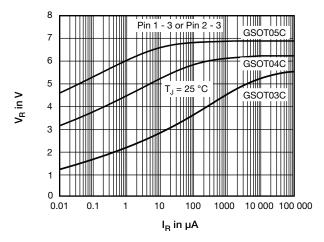
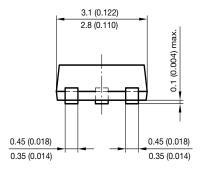
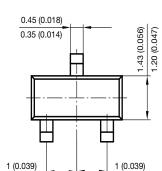


Fig. 3 - Typical Reverse Voltage $V_{\mbox{\scriptsize R}}$ vs. Reverse Current $I_{\mbox{\scriptsize R}}$

PACKAGE DIMENSIONS in millimeters (inches): SOT-23

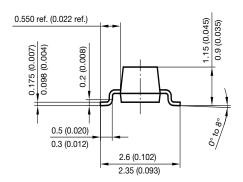


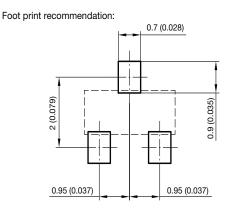


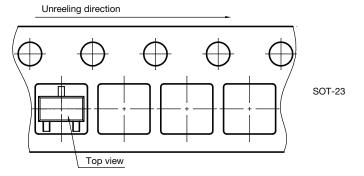
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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



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